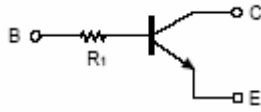




PNP Transistors

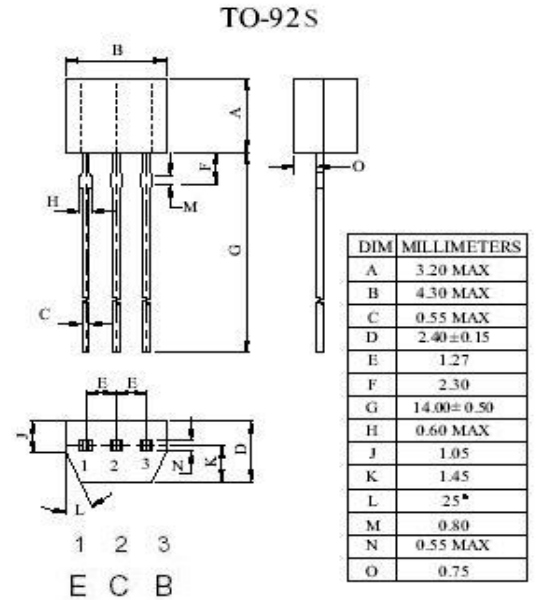
—NPN Silicon—

■■ **APPLICATION:** Interface Circuit and Driver Circuit Applications.



■■ **MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Breakdown Voltage	V_{CBO}	-50	V
Collector-Emitter Breakdown Voltage	V_{CEO}	-50	V
Emitter-Base Breakdown Voltage	V_{EBO}	-5	V
Collector Current	I_C	-0.1	A
Power Dissipation	P_C	0.3	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



■■ **ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector-Base Breakdown Voltage	BV_{CBO}	-50			V	$I_C = -50\mu A$ $I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50			V	$I_C = -1mA$ $I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	$I_E = -50\mu A$ $I_C = 0$
Collector Cut-off Current	I_{CBO}			-0.5	μA	$V_{CB} = -50V$ $I_E = 0$
Emitter Cut-off Current	I_{EBO}			-0.5	μA	$V_{EB} = -4V$ $I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	$I_C = -5mA$ $I_B = -0.5mA$
DC Current Gain	h_{FE}	100	250	600	β	$V_{CE} = -5V$ $I_C = -1mA$
Input Resistance	R_1	32.9	47	61.1	K Ω	
Gain bandwidth product	f_T		250		MHZ	$V_{CE} = 10V$ $I_E = -5mA$ $f = 100MHz$

■■ **G_T Classification And Marking**

Print Mark	A144TS
Classification	
h_{FE}	100-600